L Number	Hits	Search Text	DB	Time stamp
1	36840	Lithography	USPAT;	2003/08/19
			US-PGPUB; EPO; JPO	09:31
2	224450	Lithography and semiconductor? or wafer?	USPAT;	2003/08/19
		or chip?	US-PGPUB; EPO; JPO	09:32
3	24119	Semiconductor and lithography	USPAT;	2003/08/19
		l l l l l l l l l l l l l l l l l l l	US-PGPUB;	09:32
			EPO; JPO	33.32
4	3213	(Semiconductor and lithography) and (USPAT;	2003/08/19
_	7.00	reticle or mask near2 chamber)	US-PGPUB;	09:33
		Total of man indiff office ,	EPO; JPO	09.33
6	. 1	(((Semiconductor and lithography) and (USPAT;	2003/08/19
	_	reticle or mask near2 chamber)) and (US-PGPUB;	09:34
		chamber near2 opening)) and (opening	EPO; JPO	
		near2 panel)	220, 020	`
7	2	((Semiconductor and lithography) and (USPAT;	2003/08/19
	_	reticle or mask near2 chamber)) and (US-PGPUB;	09:49
		opening near2 panel)	EPO; JPO	
8	3135	((Semiconductor and lithography) and (USPAT;	2003/08/19
		reticle or mask near2 chamber)) and (US-PGPUB;	09:40
		reticle or mask near2 stage)	EPO; JPO	
9	. 43	(((Semiconductor and lithography) and (USPAT;	2003/08/19
		reticle or mask near2 chamber)) and (US-PGPUB;	09:40
		chamber near2 opening)) and (reticle or	EPO; JPO	
		mask near2 stage)		
10	42	((((Semiconductor and lithography) and (USPAT;	2003/08/19
		reticle or mask near2 chamber)) and (US-PGPUB;	09:42
		chamber near2 opening)) and (reticle or	EPO; JPO	
		mask near2 stage)) and (remov\$5 near3		
	_	reticle or mask)	1	
11	1	(((((Semiconductor and lithography) and (USPAT;	2003/08/19
1		reticle or mask near2 chamber)) and (US-PGPUB;	09:42
		chamber near2 opening)) and (reticle or	EPO; JPO	
		mask near2 stage)) and (remov\$5 near3		
		reticle or mask)) and (angle? near2 opening)		,
12	3	((Semiconductor and lithography) and (USPAT;	2003/08/19
		reticle or mask near2 chamber)) and (US-PGPUB;	09:46
		angle? near2 opening)	EPO; JPO	33
13	2	((Semiconductor and lithography) and (USPAT;	2003/08/19
	_	reticle or mask near2 chamber)) and (US-PGPUB;	09:46
		angle? near2 chamber)	EPO; JPO	
5	51	((Semiconductor and lithography) and (USPAT;	2003/08/19
		reticle or mask near2 chamber)) and (US-PGPUB;	10:26
		chamber near2 opening)	EPO; JPO	
14	10251	((250/492.2,492.22,492.21,492.3,396ML,)	USPAT;	2003/08/19
		or (438/4,) or (257/678,) or	US-PGPUB;	10:29
1,5		(355/53,)).CCLS.	EPO; JPO	
15	4	(((250/492.2,492.22,492.21,492.3,396ML,)	USPAT;	2003/08/19
		or (438/4,) or (257/678,) or	US-PGPUB;	10:33
	<u> </u>	(355/53,)).CCLS.) and (opening near2	EPO; JPO	
16	1814	panel (//250/492 2 492 22 492 21 492 2 206MT)	Henam.	2002/00/10
10	1014	(((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or	USPAT; US-PGPUB;	2003/08/19
	,	(355/53,)).CCLS.) and (reticle or mask	EPO; JPO	10:33
		near2 chamber)	EFO, 0FO	
17	2006	(((250/492.2,492.22,492.21,492.3,396ML,)	USPAT;	2003/08/19
	2000	or (438/4,) or (257/678,) or	US-PGPUB;	10:34
		(355/53,)).CCLS.) and (reticle or mask	EPO; JPO	
		near2 stage)	====, ===	
18	3582	(((250/492.2,492.22,492.21,492.3,396ML,)	USPAT;	2003/08/19
		or (438/4,) or (257/678,) or	US-PGPUB;	10:35
		(355/53,)).CCLS.) and (remov\$4 near3	EPO; JPO	
		reticle or mask)		
		in		<u> </u>

10/056,017

19	2	(((((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or	USPAT; US-PGPUB;	2003/08/19 10:37
		(355/53,)).CCLS.) and (remov\$4 near3 reticle or mask)) and (angle? near2 chamber)	EPO; JPO	
20	7	((((250/492.2,492.22,492.21,492.3,396ML,)) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (remov\$4 near3 reticle or mask)) and (angle? near2	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:37
		stage)		